

600V, 40A, Trench FS II IGBT

General Description:

Using H&M SEMI's proprietary trench design and advanced FS (fieldstop)second generation technology, the 600V Trench FSII IGBT offers superior conduction and switching performances, and easy parallel operation;

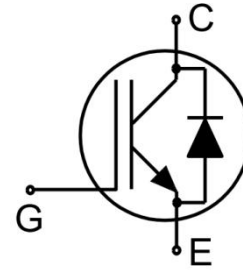
Features

Trench FSII Technology offering

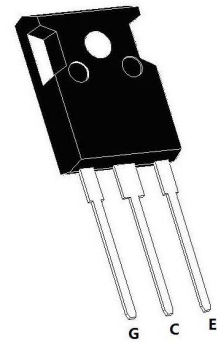
- Very low $V_{CE(sat)}$
- High speed switching
- Positive temperature coefficient in $V_{CE(sat)}$
- Very tight parameter distribution
- High ruggedness, temperature stable behavior

Application

- Uninterruptible Power Supplies (UPS)
- Welding Converters
- Inverters



Schematic diagram



TO-247-3L top view

Package Marking and Ordering Information

Device	V_{CE}	I_C	Device Marking	Device Package
HMG40N60T	600V	40A	HMG40N60T	TO-247-3L

Absolute Maximum Ratings (TC=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{CES}	Collector-Emitter Voltage	600	V
V_{GES}	Gate- Emitter Voltage	±30	V
I_C	Collector Current	80	A
	Collector Current @ $T_C = 100\text{ }^\circ\text{C}$	40	A
I_{Cplus}	Pulsed Collector Current, t_p limited by T_{jmax}	160	A
-	turn off safe operating area, $V_{CE}=600V$, $T_j=150\text{ }^\circ\text{C}$	160	A
I_C	Pulsed Collector Current	160	A
I_F	Diode Continuous Forward Current @ $T_C = 100\text{ }^\circ\text{C}$	40	A
I_{FM}	Diode Maximum Forward Current	150	A
P_D	Power Dissipation @ $T_C = 25\text{ }^\circ\text{C}$	306	W
	Power Dissipation @ $T_C = 100\text{ }^\circ\text{C}$	122	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Temperature for Soldering	260	$^\circ\text{C}$
t_{sc}	Short circuit withstand time $V_{GE}=15.0V$, $V_{CC}\leq 400V$, Allowed number of short circuits<1000Time between short circuits: $\geq 1.0s, T_{vj}\leq 150\text{ }^\circ\text{C}$	10	us

Thermal Characteristic

Symbol	Parameter	Typ.	Max.	Units
R _{θJC}	Thermal Resistance, Junction to case for IGBT	--	0.41	°C/W
R _{θJC}	Thermal Resistance, Junction to case for Diode	--	1.45	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	--	40	°C/W

Electrical Characteristics (T_c=25°C unless otherwise noted)

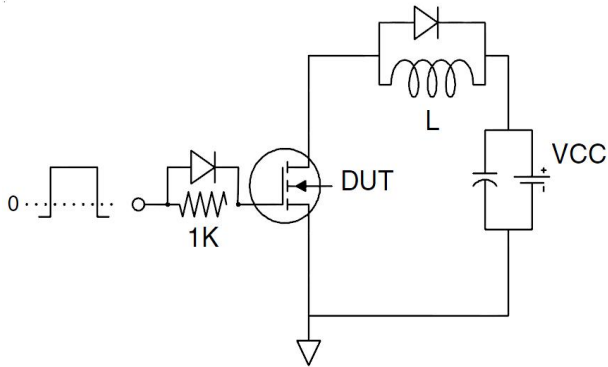
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
OFF Characteristics						
V _{(BR)CES}	Collector-Emitter Breakdown Voltage	V _{GE} =0V, I _{CE} =1mA	600	--	--	V
I _{CES}	Collector-Emitter Leakage Current	V _{GE} =0V, V _{CE} =600V	--	--	4	μA
I _{GES(F)}	Gate to Emitter Forward Leakage	V _{GE} =+30V, V _{CE} =0V	--	--	100	nA
I _{GES(R)}	Gate to Source Reverse Leakage	V _{GE} =-30V, V _{CE} =0V	--	--	100	nA
ON Characteristics						
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C =40A, V _{GE} =15V	--	1.7	1.9	V
V _{GE(th)}	Gate Threshold Voltage	I _C =1mA, V _{CE} =V _{GE}	4.0	5.0	6.0	V
Dynamic Characteristics						
C _{ies}	Input Capacitance	V _{CE} =25V, V _{GE} =0V, f=1MHz	--	1900	--	pF
C _{oes}	Output Capacitance		--	151	--	
C _{res}	Reverse Transfer Capacitance		--	90	--	
Q _{Gate}	Gate charge	V _{CC} =480V, I _C =40A V _{GE} =15V	--	195	--	nC
I _{C(SC)}	Short circuit collector current Max.1000 short circuits Time between short circuits: ≥1.0s	V _{GE} =15V, V _{CC} ≤400V, t _{SC} ≤10us, T _J ≤150°C	--	190	--	A
Switching Characteristics						
t _{d(ON)}	Turn-on Delay Time	V _{CE} =400V, I _C =40A V _{GE} =0/15V, R _g =8Ω Inductive Load	--	21	--	ns
t _r	Rise Time		--	34	--	
t _{d(OFF)}	Turn-Off Delay Time		--	203	--	
t _f	Fall Time		--	23	--	
E _{on}	Turn-On Switching Loss		--	1.12	--	mJ
E _{off}	Turn-Off Switching Loss		--	0.61	--	
E _{ts}	Total Switching Loss		--	1.73	--	

Electrical Characteristics of the Diode (T_c= 25°C unless otherwise specified) :

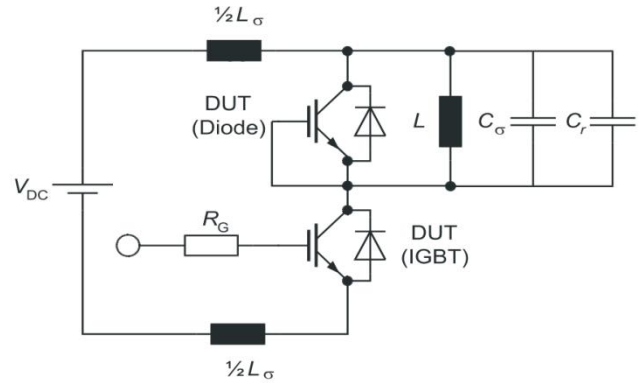
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V _{FM}	Diode Forward Voltage	I _F =20A	--	1.6	2.0	V
T _{rr}	Reverse Recovery Time	V _{ce} =400V, I _F =20A, di/dt=1000A/μS	--	151	--	ns
I _{RRM}	Diode Peak Reverse Recovery Current		--	15.5	--	A
Q _{rr}	Reverse Recovery Charge		--	1.23	--	μC
Pulse width t _p ≤380μs, δ≤2%						

Test Circuit

1) Gate Charge Test Circuit

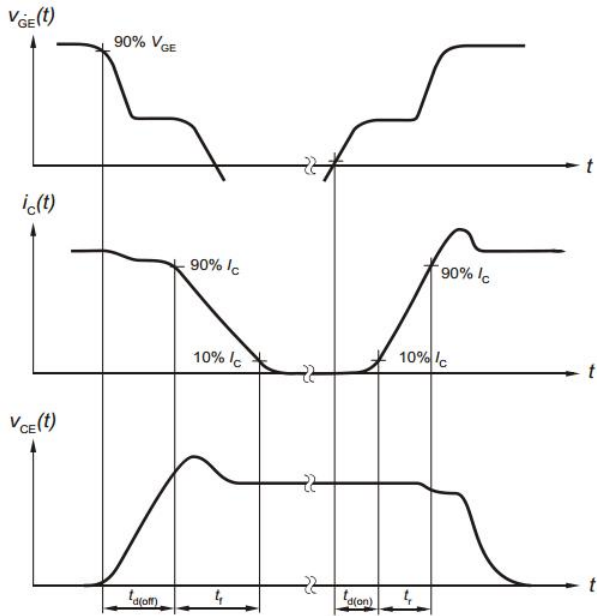


2) Switch Time Test Circuit

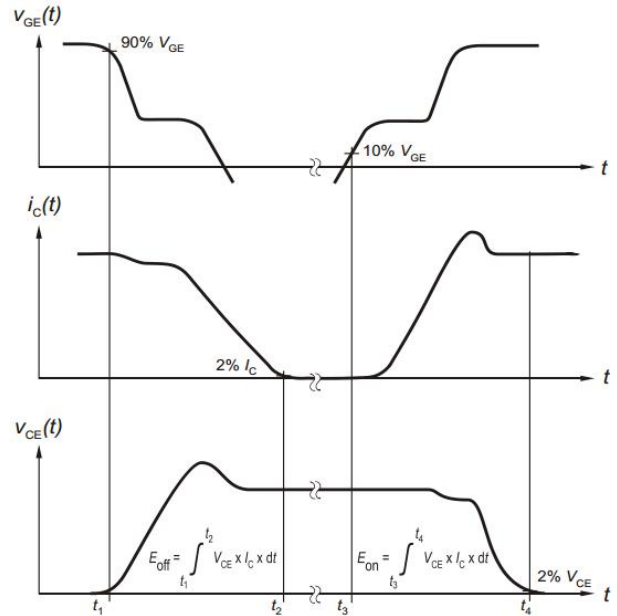


Switching characteristics

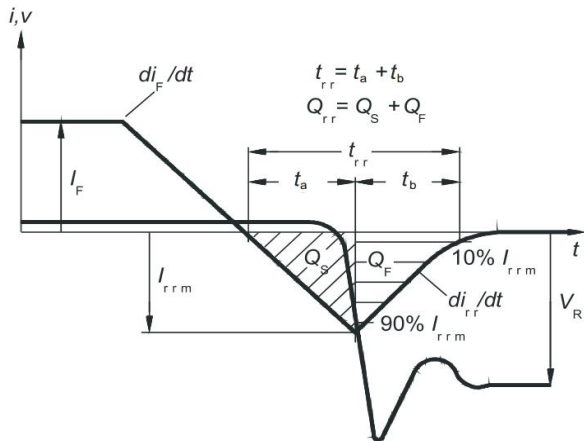
1) definition of switching times



2) definition of switching losses



3) Definition of diode switching characteristics



Typical Electrical and Thermal Characteristics

Figure 1 Output Characteristics

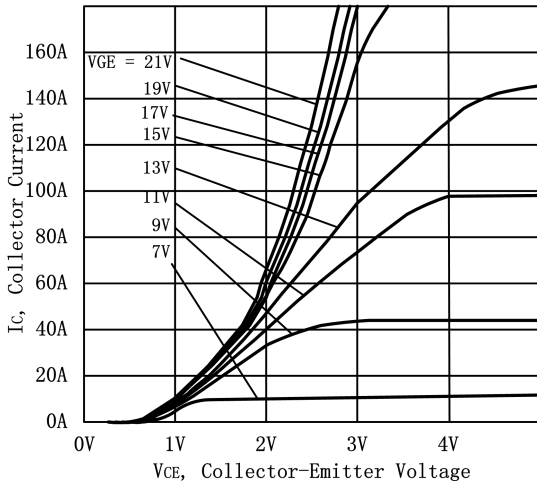


Figure 2. Transfer Characteristics

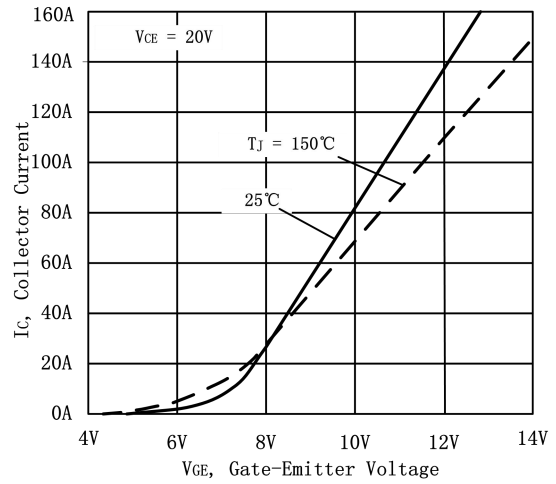


Figure 3 V_{CEsat} vs. Case Temperature

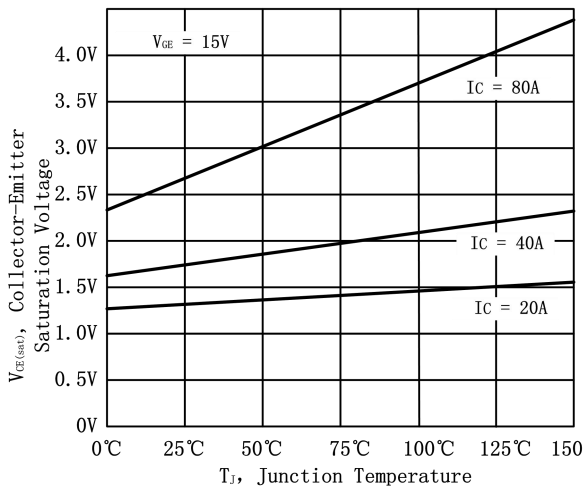


Figure 4 Saturation Voltage vs. VGE

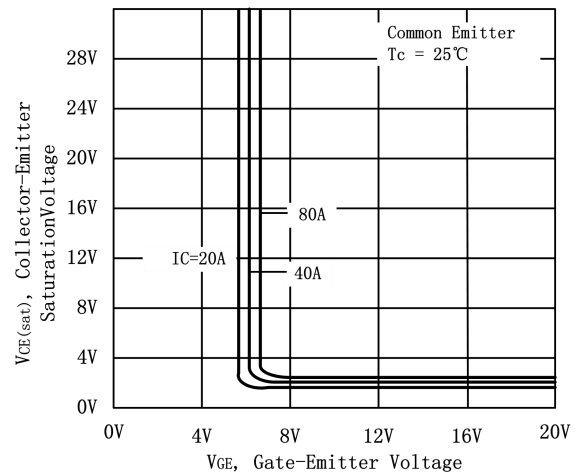


Figure 5 Capacitance Characteristics

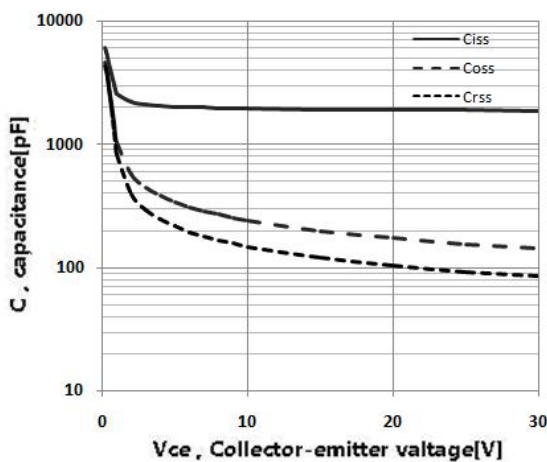
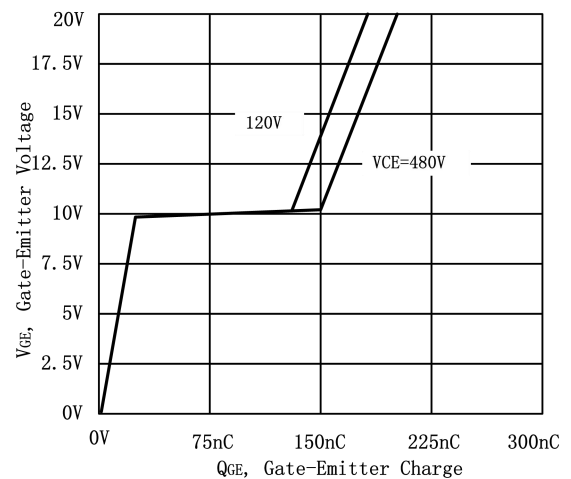


Figure 6 Gate charge waveform



Typical Electrical and Thermal Characteristics (continued)

Figure 7. Forward Characteristics

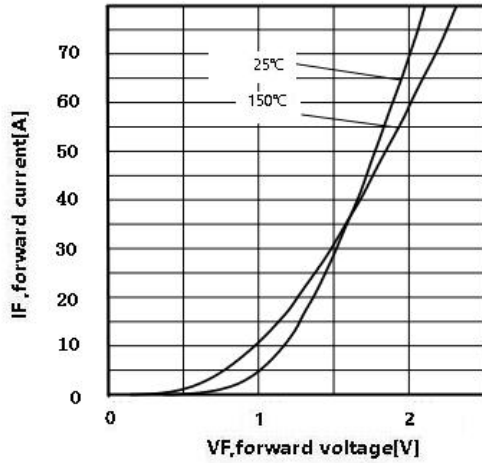


Figure 8 V_F vs. temperature

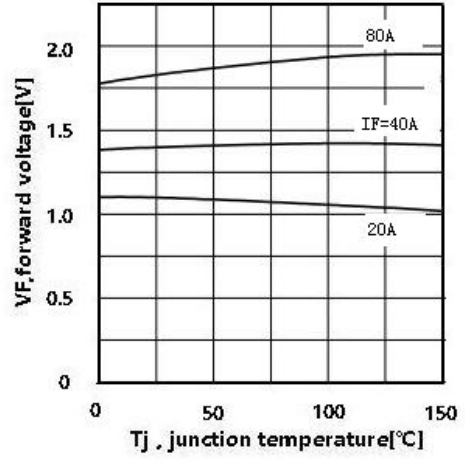
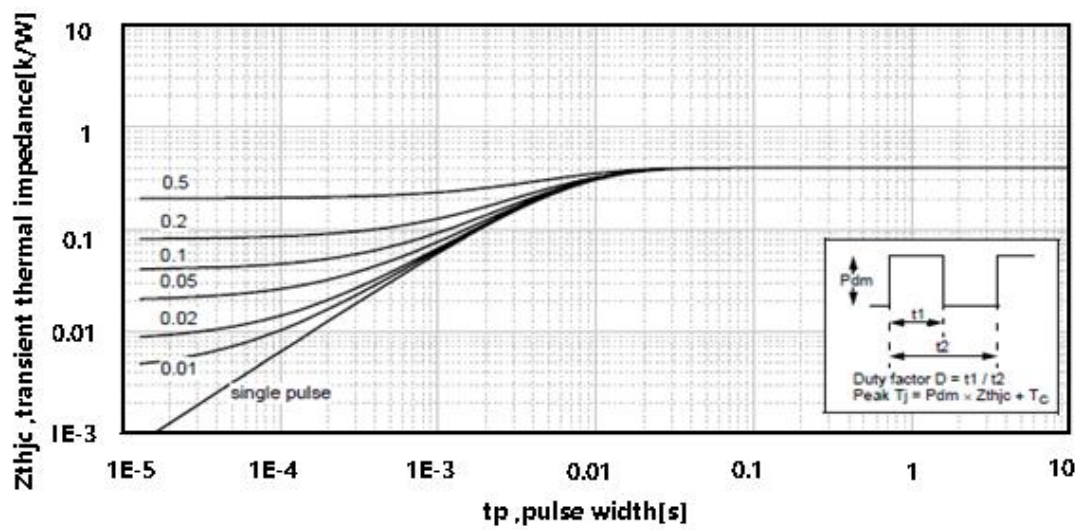
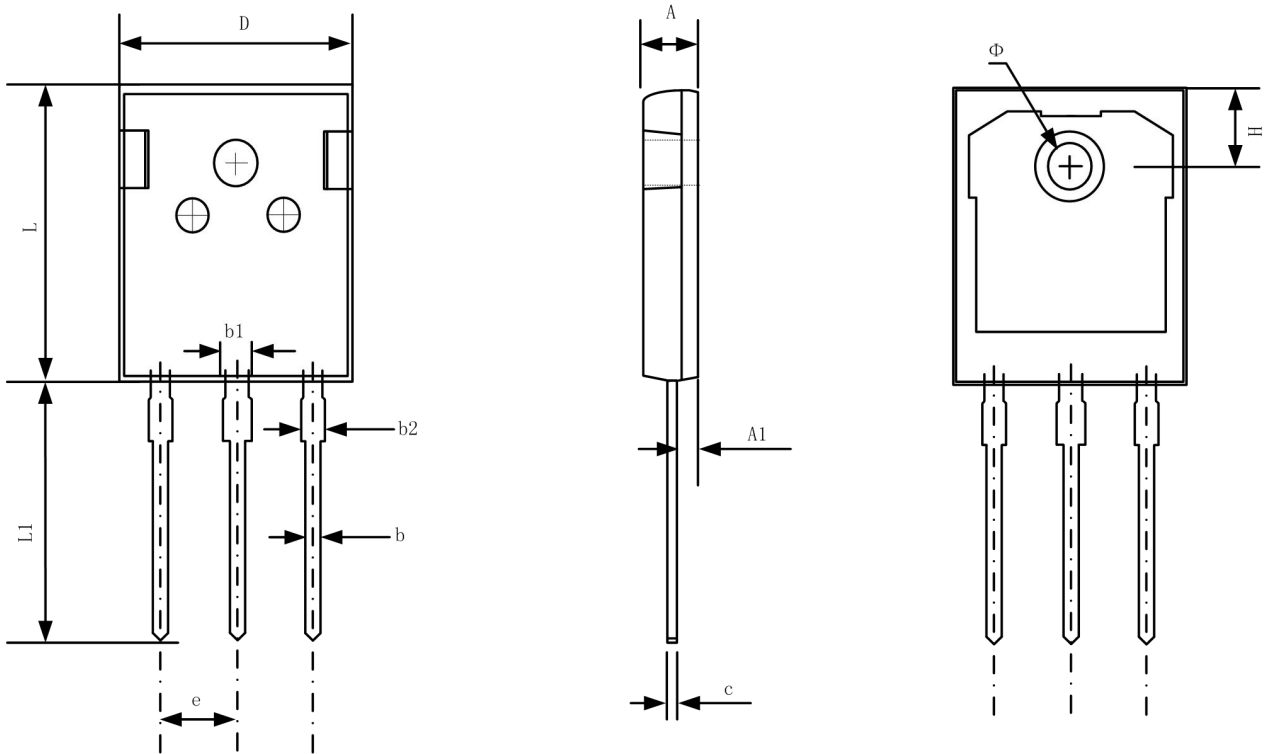


Figure 9. Transient Thermal Impedance of IGBT



TO-247-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.800	5.200	0.189	0.205
A1	2.210	2.610	0.087	0.103
b	1.700	1.900	0.067	0.075
b1	2.800	3.200	0.110	0.126
b2	1.800	2.200	0.071	0.087
c	0.500	0.700	0.020	0.028
D	15.600	16.000	0.614	0.630
L	20.800	21.200	0.819	0.835
L1	19.620	20.220	0.772	0.796
Φ	3.450	3.750	0.136	0.148
e	5.440 TYP		0.214 TYP	
H	6.150 REF		0.242 REF	